

<b>FORM PTO-1449 (SUBSTITUTE)</b>  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  <b>INFORMATION DISCLOSURE          STATEMENT BY APPLICANT</b> (37 CFR 1.98(b))				Attorney Docket No.: P2001,0004 Appl. No.: <u>10-614430</u>  Applicant: ALEXANDAR RUF ET AL.  Filing Date: July 7, 2003 Group Art Unit: <u>2826</u>			
EXAMINER INITIALS	A	PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
<u>CAL</u>	A	6,121,134	9/19/00	Burton et al.	<del>          </del>	<del>          </del>	<del>          </del>
<u>CAL</u>	B	5,639,678	6/17/97	Lee et al.	<del>          </del>	<del>          </del>	<del>          </del>
<u>CAL</u>	C	4,701,349	10/20/87	Koyanagi et al.	<del>          </del>	<del>          </del>	<del>          </del>
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<b>FOREIGN PATENT DOCUMENT</b>							
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES   NO
	J						
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	M						
	N						
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
<u>CAL</u>		Kaneko, H. et al.: "Novel Submicrometer MOS Devices by Self-Aligned Nitridation of Silicide", IEEE, Transactions on Electron Devices, Vol. ED-33, No. 11, November 1986, pp. 1702-1709					
<u>CAL</u>		Kamgar, A. et al.: "Self-Aligned TiN Barrier Formation by Rapid Thermal Nitridation of TiSi <sub>2</sub> in Ammonia", American Institute of Physics, J. Appl. Phys., Vol. 66, No. 6, September 15, 1989, pp. 2395-2401					
EXAMINER <u>[Signature]</u>				DATE CONSIDERED <u>9/29/04</u>			

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U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEINFORMATION DISCLOSURE  
STATEMENT BY APPLICANT  
(37 CFR 1.98(b))

Attorney Docket No.: P2001,0004

Appl. No.: 10-614430

Applicant: ALEXANDAR RUF ET AL.

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## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

<u>Cal</u>		Inoue, K. et al.: "A New Cobalt Salicide Technology for 0.15- $\mu$ m CMOS Devices", IEEE Transactions on Electron Devices, Vol. 45, No. 11, November, 11 1998, pp. 2312-2318
<u>Cal</u>		Chen, S. C. et al.: "Formation of Titanium Nitride/Titanium Silicide by High Pressure Nitridation in Titanium/Silicon", Japanese Journal of Applied Physics, Vol. 30, No. 11A, November 1991, pp. 2673-2678

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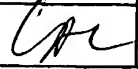
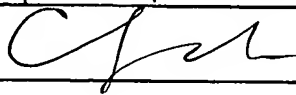
## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

<i>Cal</i>		Tolia, A. et al.: "Integrated IMP Ti and MOCVD TiN for 300mm W Barrier and Liner for Sub 0.18 $\mu$ m IC Processing", SPIE, Vol. 3883, September 1999, pp. 130-136
<i>Cal</i>		Kanamura, R. et al.: "Influence of the Sputtering Method of TiN/Ti Films on the Resistance of High Aspect Ratio Contact Holes", VMIC Conference, June 18-20 1996, pp. 554-559

EXAMINER *Cal*

DATE CONSIDERED

*9/29/04*

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<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
		Gambino, J. et al.: "Tungsten Contacts for a 256m DRAM Process Using a Thermally Formed TiN Diffusion Barrier", VMIC Conference, June 18-20, 1996; pp. 180i-180k					
		Dixit, G. A. et al.: "Ion Metal Plasma (IMP) Deposited Titanium Liners for 0.25/0.18 µm Multilevel Interconnections", IEEE, 1996, pp. 14.3.1-14.3.4					
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<i>CAH</i>		Author not listed: "Physical Vapor Deposition Process BKM: Vectra IMP Ti", Applied Materials Inc., 2000, pp. 1-30					
<i>CAH</i>		Ermolieff, A. et al.: "Nitridation of Polycrystalline Titanium as Studied by in situ Angle-Resolved X-ray Photoelectron Spectroscopy", John Wiley & Sons, Ltd., Surface and Interface Analysis, Vol. 11, January 18, 1988, pp. 563-568					
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